



SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

ECH8420 — N-Channel Silicon MOSFET General-Purpose Switching Device Applications

Features

- ON-resistance $R_{DS(on)1}=5.2m\Omega$ (typ.)
- 1.8V drive
- Halogen free compliance

Specifications

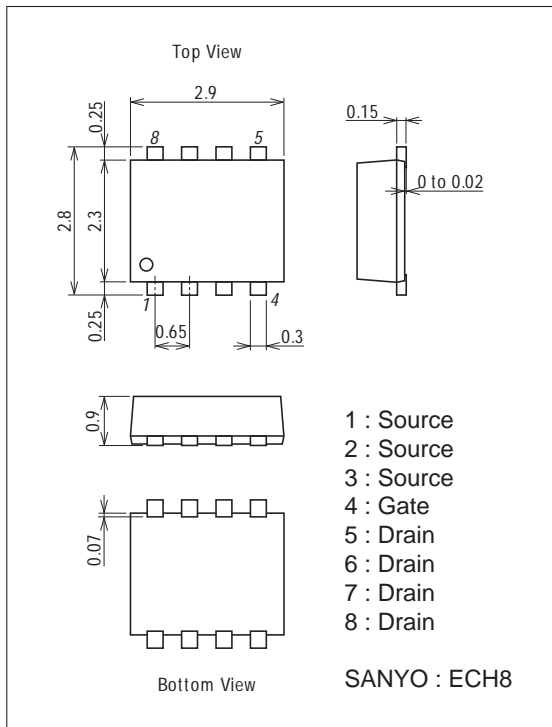
Absolute Maximum Ratings at $T_a=25^\circ C$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		20	V
Gate-to-Source Voltage	V_{GSS}		± 12	V
Drain Current (DC)	I_D		14	A
Drain Current (Pulse)	I_{DP}	$PW \leq 10\mu s$, duty cycle $\leq 1\%$	50	A
Allowable Power Dissipation	P_D	When mounted on ceramic substrate (900mm ² ×0.8mm)	1.6	W
Channel Temperature	T_{ch}		150	°C
Storage Temperature	T_{stg}		-55 to +150	°C

Package Dimensions

unit : mm (typ)

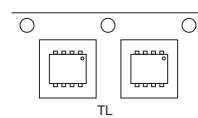
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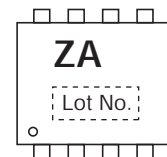
Product & Package Information

- Package : ECH8
- JEITA, JEDEC : -
- Minimum Packing Quantity : 3,000 pcs./reel

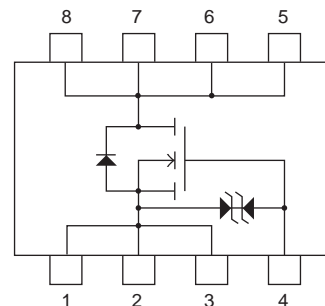
Packing Type : TL



Marking



Electrical Connection

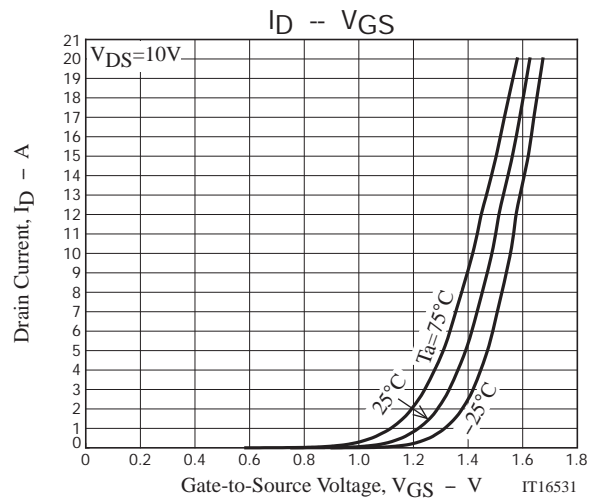
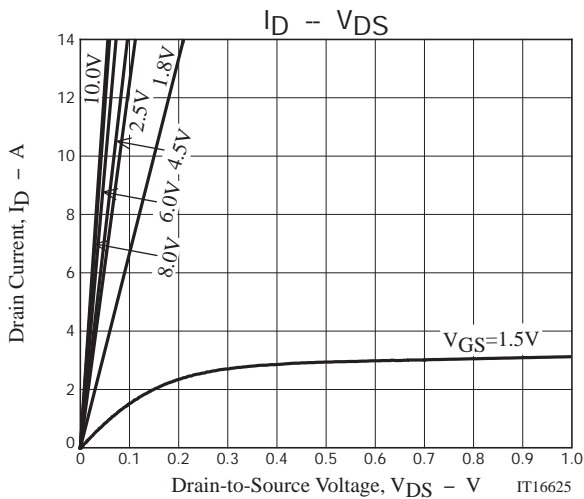
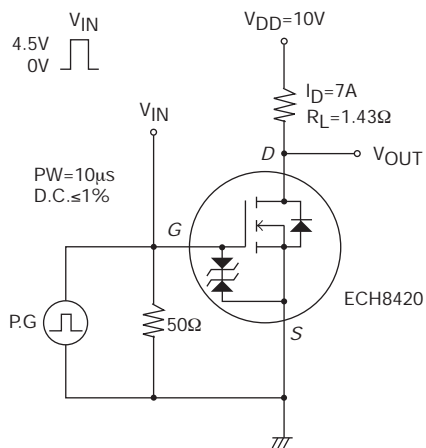


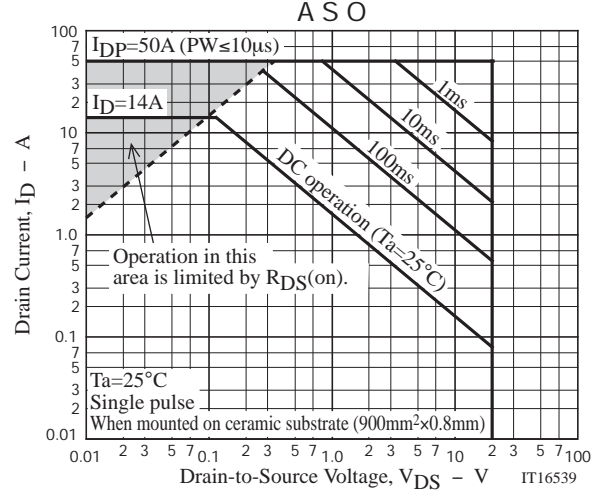
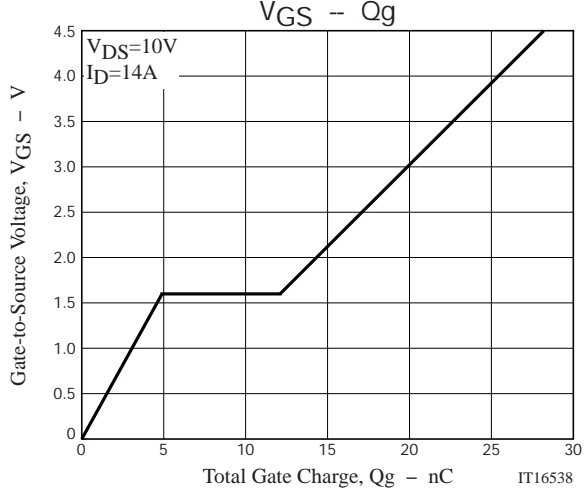
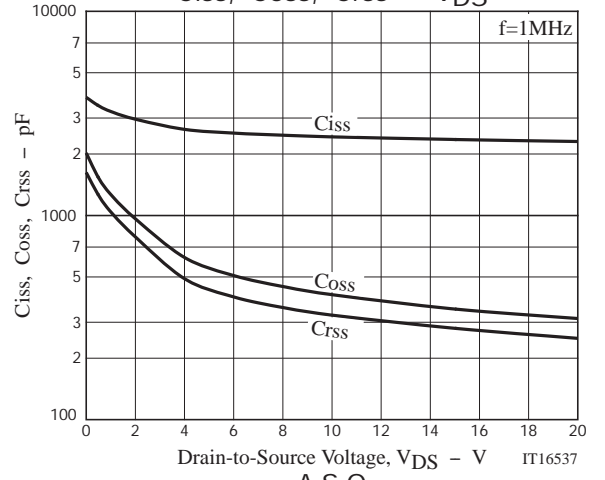
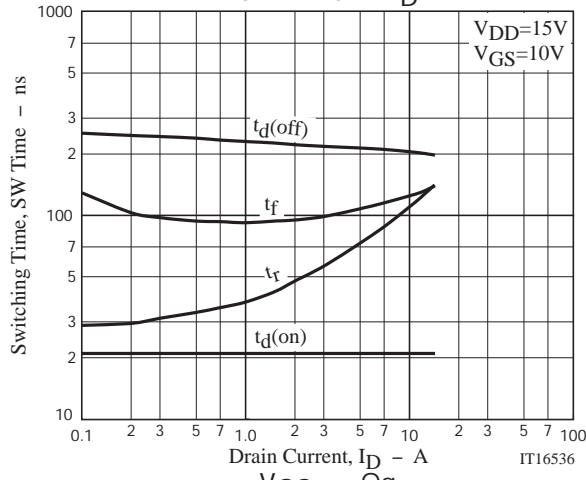
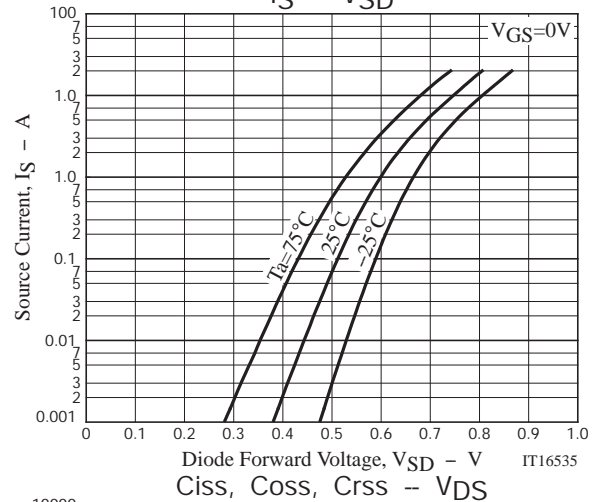
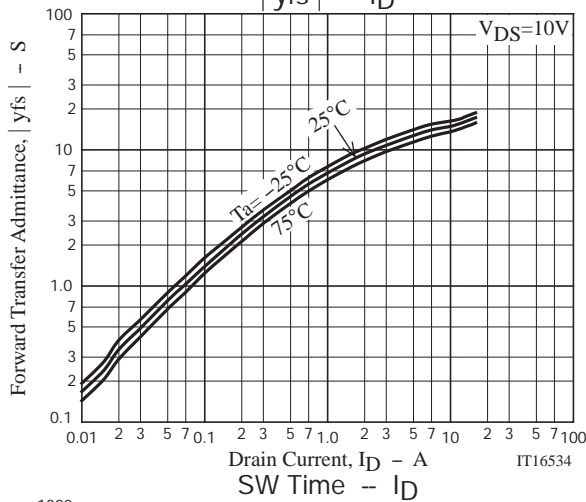
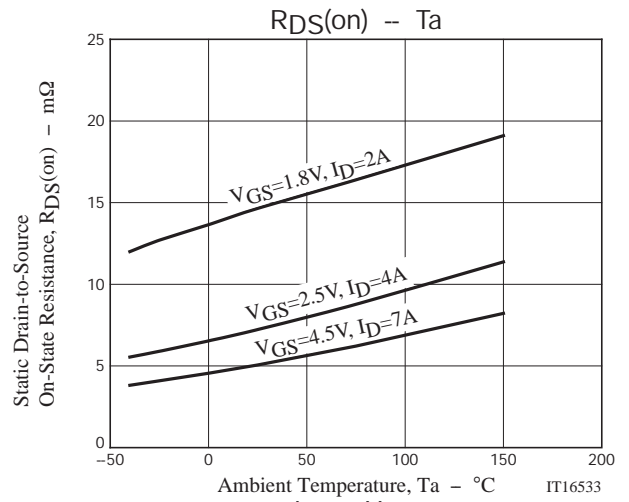
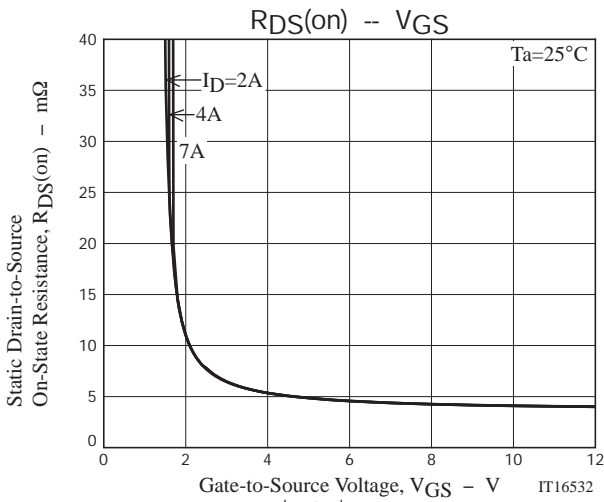
ECH8420

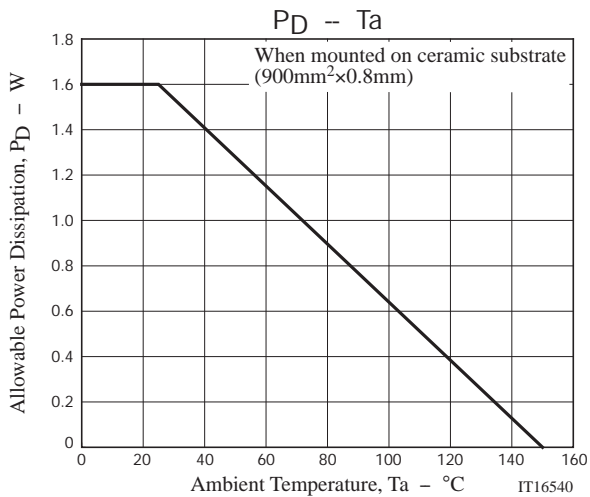
Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=1mA, V_{GS}=0V$	20			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=20V, V_{GS}=0V$			1	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 8V, V_{DS}=0V$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10V, I_D=1mA$	0.4		1.3	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=10V, I_D=7A$		14.5		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=7A, V_{GS}=4.5V$		5.2	6.8	$m\Omega$
	$R_{DS(on)2}$	$I_D=4A, V_{GS}=2.5V$		8	11.5	$m\Omega$
	$R_{DS(on)3}$	$I_D=2A, V_{GS}=1.8V$		15	22.5	$m\Omega$
Input Capacitance	C_{iss}	$V_{DS}=10V, f=1MHz$		2430		pF
Output Capacitance	C_{oss}			410		pF
Reverse Transfer Capacitance	C_{rss}			330		pF
Turn-ON Delay Time	$t_d(on)$			21		ns
Rise Time	t_r	See specified Test Circuit.		88		ns
Turn-OFF Delay Time	$t_d(off)$			210		ns
Fall Time	t_f			115		ns
Total Gate Charge	Q_g		$V_{DS}=10V, V_{GS}=4.5V, I_D=14A$		29	
Gate-to-Source Charge	Q_{gs}			4.8		nC
Gate-to-Drain "Miller" Charge	Q_{gd}			8.7		nC
Diode Forward Voltage	V_{SD}	$I_S=14A, V_{GS}=0V$			0.75	1.2

Switching Time Test Circuit







Note on usage : Since the ECH8420 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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